Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	827	"silicon nitride" same "silicon oxide" same "etch stoP"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 15:50
L4	598	("silicon nitride" or "silicon oxide" or "etch stoP") same gates same spacers	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 15:51
L5	132	("silicon nitride" or "silicon oxide") same gates same spacers same implant$4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 16:00
L6	261	("silicon nitride" or "silicon oxide") and gates and spacers and implant$4 and "hard mask"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 15:56
L7	2867	("silicon nitride" or "etch stop") and gates and spacers and pattern$4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 15:58
L8	2001	("silicon nitride" or "etch stop") and gates and spacers and pattern$4 and (trench or via)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 15:59
L9	1311	8 and "438"/$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 15:59
L10	116	("silicon nitride" or "etch stop") same gates same spacers same implant$4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 16:00
L11	500	("silicon nitride" or "etch stop") same gates same spacers	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 16:00
L12	1	koh-kwang-ok.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 16:01
L13	0	kwak-kun-ho.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 16:01
L14	3	hwang-byung-jun.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/14 16:01